

N-Channel Super Junction Power MOSFET

Description

IRF600R65C is power MOSFET using advanced super junction technology that can realize very low on-resistance and gate charge. It will provide much high efficiency by using optimized charge coupling technology. These user friendly devices give an advantage of low EMI to designers as well as low switching loss.

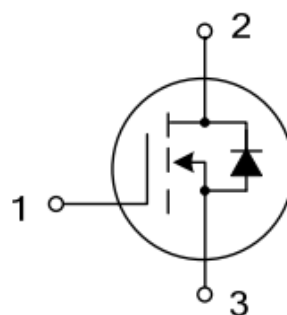
I_D	7A
V_{DSS}	650V
$R_{ds(on)(max)}$	$0.6\Omega (V_{GS}=10V, I_D=3.5A)$
Q_g	25nC

General Features

- 7A, 650V, $R_{DS(on)(max)} = 0.6\Omega @ V_{GS}=10V$
- Low Gate charge
- Low C_{rss}
- Fast Switching
- Improved dv/dt Capability

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



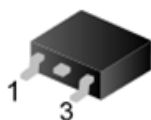
1.Gate 2.Drain 3.Source



TO-220



TO-220F



TO-252

Order Information

Order Information	Marking ID	Package	Packing Type Supplied As
SM600R65CT9RL	600R65C	TO252-2L	3000 Units on Reel
SM600R65CT2TL	600R65C	TO220F-3L	1000 units on Box、 5000 units on Carton
SM600R65CT1TL	600R65C	TO220-3L	1000 units on Box、 5000 units on Carton

Absolute Maximum Ratings Ta=25 °C unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source Voltage	V _{DS}	650	V
Gate-source Voltage	V _{GS}	±30	V
Continuous Drain Current(Ta=25°C)	I _D	7	A
Drain Current-Pulsed	I _{DM}	21	A
Total Dissipation (Ta=25°C)	TO252	52	W
	TO220	63	
	TO220F	28	
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-65 to 150	°C
Single Pulse Avalanche Energy	E _{AS}	165	mJ
ESD HBM(Human Body Mode)		≥2000	V
ESD MM(Machine Mode)		≥200	V

Electrical Characteristics Ta = 25°C

PARAMETER	Symbol	Test Condition	MIN	Typ	MAX	UNIT
Drain-source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	650			V
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =250μA	2.0		4.0	V
Drain-source Leakage Current	I _{DSS}	V _{DS} =650V, V _{GS} =0V			1	uA
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =7A			1.3	V
Gate-body Leakage Current (V _{DS} = 0)	I _{GSS}	V _{GS} =±30V			±100	nA
Static Drain-source On Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =3.5A			0.6	Ω

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant in temperature etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings

Thermal Characteristics Ta=25°C

PARAMETER		Symbol	TYP	MAX	UNIT
Maximum Junction-to-case	TO252	R _{QJC}		2.5	°C/W
	TO220F,TO220			3.1	°C/W
Maximum Junction-to-Ambient	TO252	R _{QJA}		63	°C/W
	TO220F,TO220			80	°C/W

Note1: Ensure that the channel temperature does not exceed 150°C

Note2: V_{DD}=50V, T_{ch}=25 °C(initial), I_{AS}=7A, R_g=25Ω

Note3: This transistor is sensitive to electrostatic and should be handled with care

Dynamic Characteristics Ta = 25 °C

PARAMETER	Symbol	Test Condition	MIN	TYP	MAX	UNIT
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f=1.0MHZ		380		pF
output Capacitance	C _{oss}			110		pF
Reverse Transfer Capacitance	C _{rss}			7		pF

Switching Characteristics Ta=25 °C

PARAMETER	Symbol	Test Condition	MIN	TYP	MAX	UNIT
Turn-On Delay Time	T _{d(on)}	V _{DS} =400V, I _D =7A, V _{GS} =10V, R _G =20Ω		13		nS
Turn-On Rise Time	T _r			10		nS
Turn-Off Delay Time	T _{d(off)}			85		nS
Turn-Off Rise Time	T _f			14		nS
Total Gate Charge	Q _g	V _{DS} =480V, I _D =7A, V _{GS} =10V		25		nC
Gate-Source Charge	Q _{gs}			2		nC
Gate-Drain Charge	Q _{gd}			2.7		nC

Drain-Source Diode Maximum Ratings and Characteristics Ta=25 °C

PARAMETER	Symbol	Test Condition	MIN	TYP	MAX	UNIT
Max. Diode Forward Current	I _s	Integral Reverse P-N Junction Diode in the MOSFET			7	A
Pulsed Source Current	I _{sm}				21	
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _s =7A		0	1.3	V
Reverse Recovery Time	T _{rr}	V _{GS} =0V, I _s =7A, dI _F /dt=100A/μs		190		nS
Reverse Recovery Charge	Q _{rr}			2.3		μC

Typical Characteristics Curve

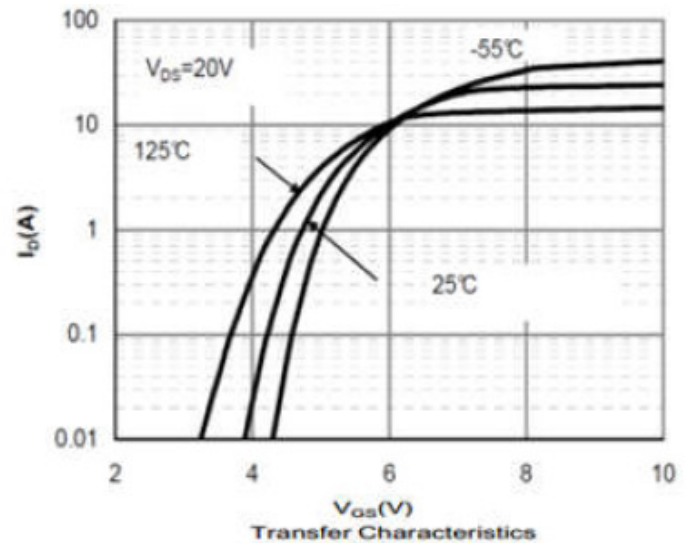
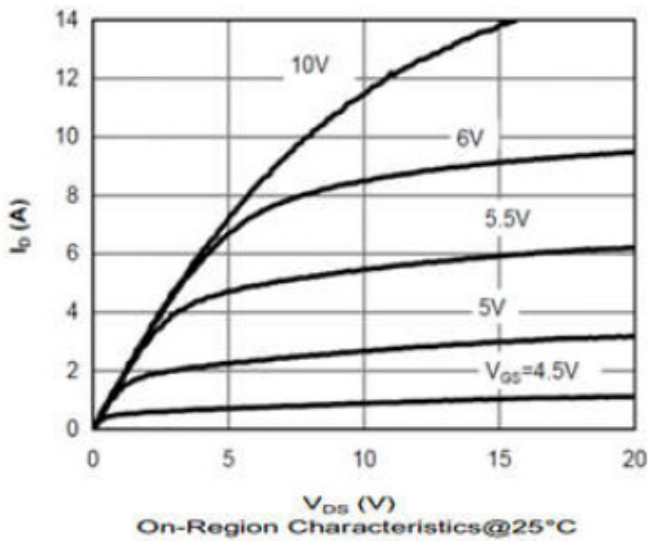


Figure 1: Output Characteristics
Figure 2: Transfer Characteristics

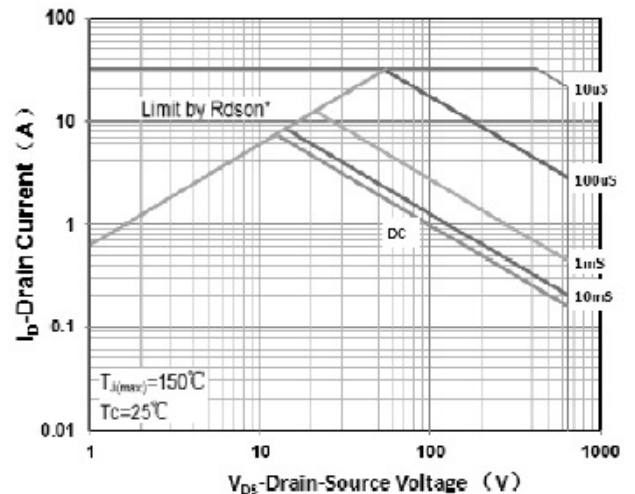
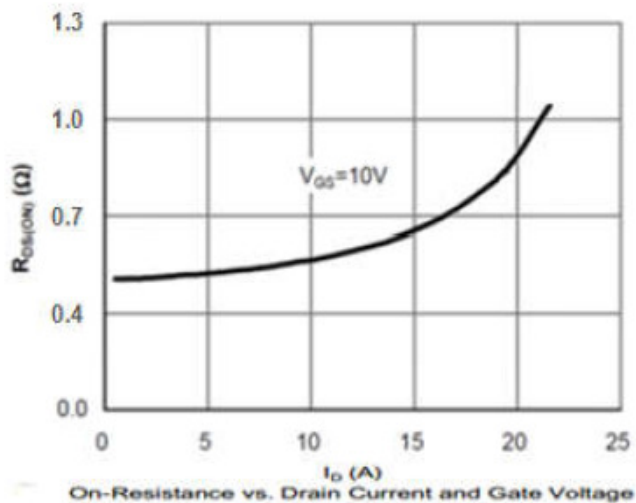


Figure 3: On Resistance Vs Drain Current
Operating Area

Figure 4: Safe

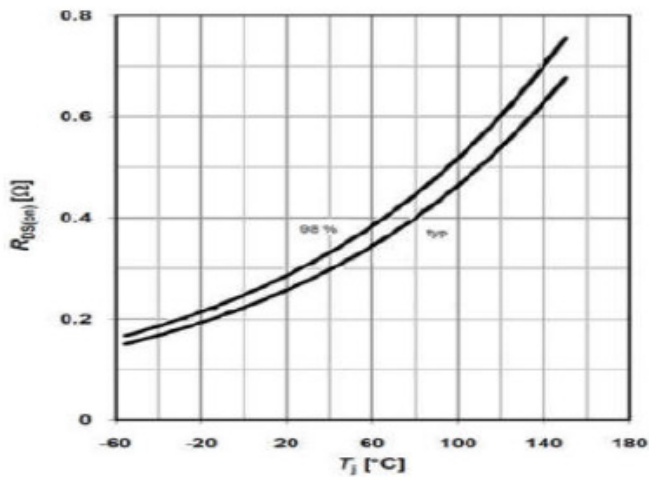


Figure5: On Resistance Vs Junction Temperature Characteristics

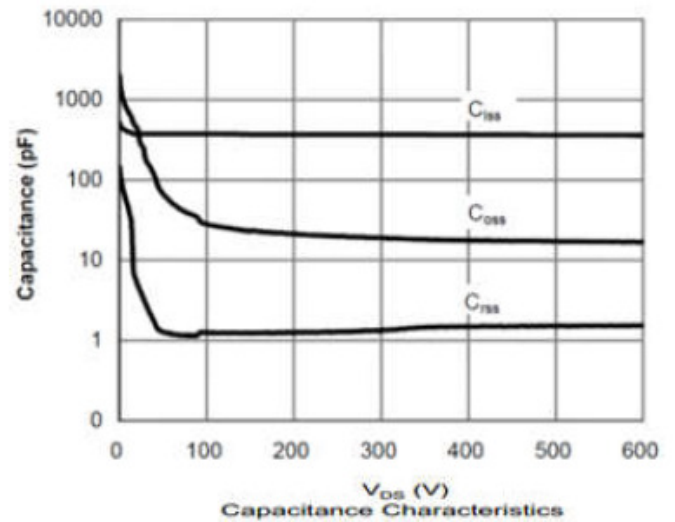


Figure6: Capacitance

Typical Characteristics Curve

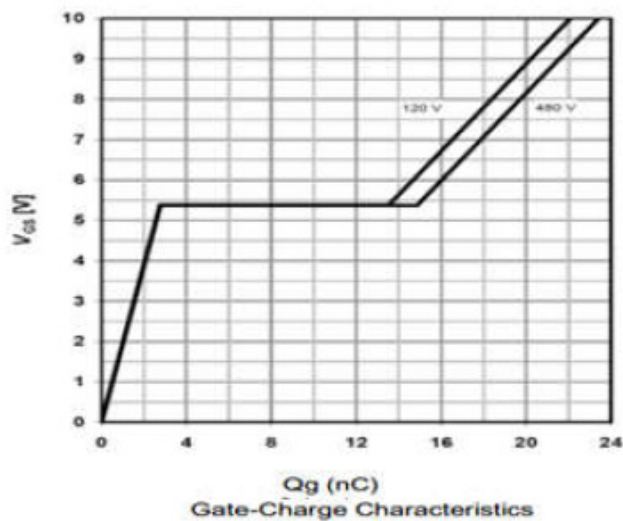


Figure7: Gate Charge Waveform Forward Voltage

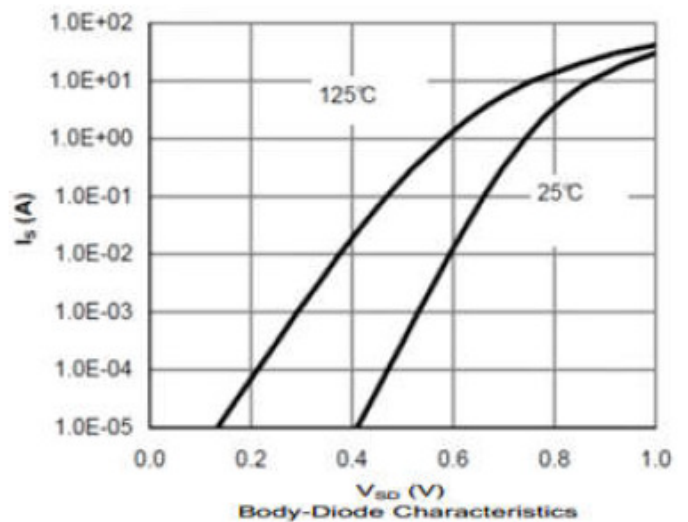


Figure8: Source-Drain Diode

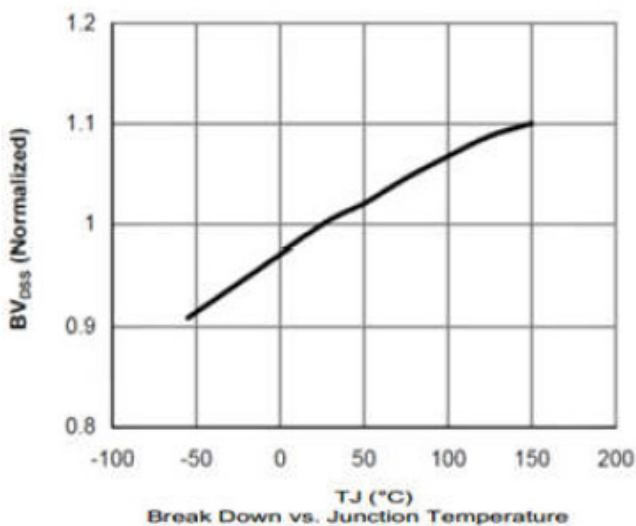
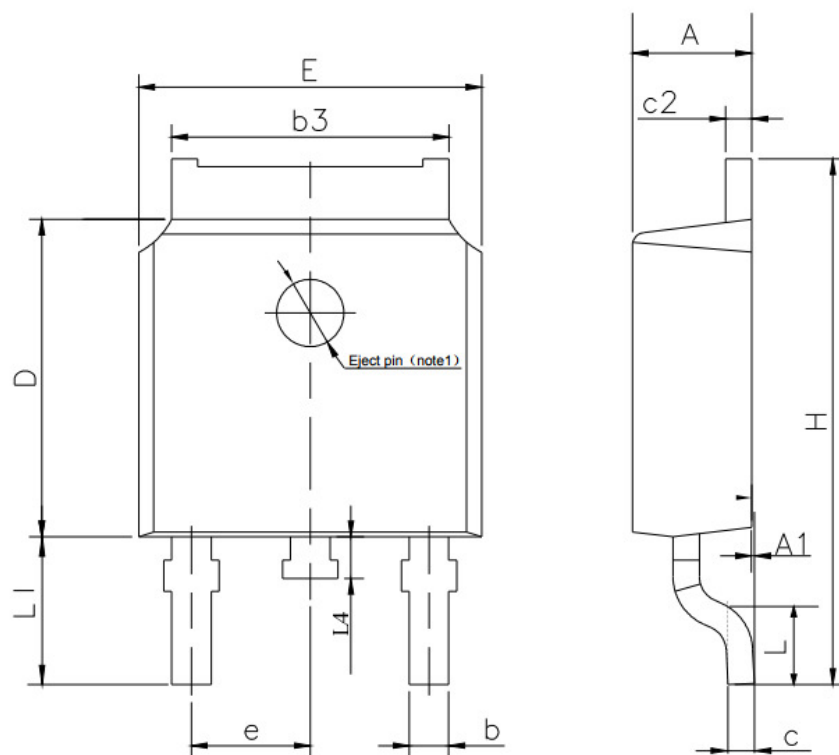


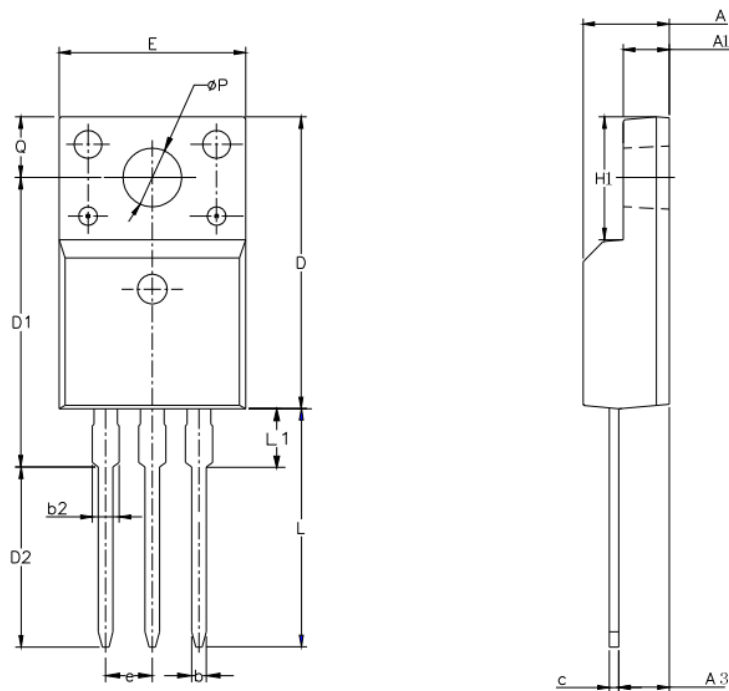
Figure9: Breakdown Voltage Vs Junction Temperature

Outline Information (TO252-2L)



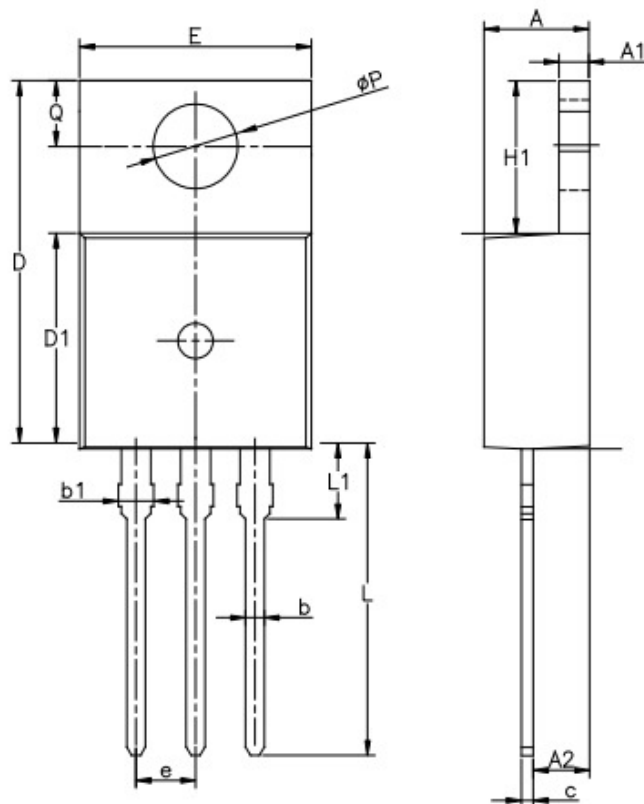
SYMBOL	MIN	NOM	MAX
A	2.10	2.30	2.50
A1	0	---	0.127
b	0.66	0.76	0.89
b3	5.10	5.33	5.46
c	0.45	---	0.65
c2	0.45	---	0.65
D	5.80	6.10	6.40
E	6.30	6.60	6.90
e	2.30TYP		
H	9.60	10.10	10.60
L	1.40	1.50	1.70
L1	2.90REF		
L4	0.60	0.80	1.00

Outline Information (TO220F-3L)



SYMBOL	MIN	NOM	MAX
A	4.42	4.70	5.02
A1	2.30	2.54	2.80
A3	2.50	2.76	3.10
b	0.70	0.80	0.90
b2	—	—	1.47
c	0.35	0.50	0.65
D	15.25	15.87	16.25
D1	15.30	15.75	16.30
D2	9.30	9.80	10.30
E	9.73	10.16	10.36
e	2.54BCS		
H1	6.40	6.68	7.00
L	12.48	12.98	13.48
L1	/	/	3.50
ϕP	3.00	3.18	3.40
Q	3.05	3.30	3.55

Outline Information (TO220-3L)



SYMBOL	MIN	NOM	MAX
A	4.30	4.50	4.70
A1	1.00	1.30	1.50
A2	1.80	2.40	2.80
b	0.60	0.80	1.00
b1	1.00	—	1.60
c	0.30	—	0.70
D	15.10	15.70	16.10
D1	8.10	9.20	10.00
E	9.60	9.90	10.40
e	2.54BSC		
H1	6.10	6.50	7.00
L	12.60	13.08	13.60
L1	—	—	3.95
ϕP	3.40	3.70	3.90
Q	2.60	—	3.20